

# RF power transistor from the LdmoST family of N-channel enhancement-mode lateral MOSFETs

Datasheet — production data

#### **Features**

- Excellent thermal stability
- Common source configuration
- P<sub>OUT</sub> (@ 28 V)= 70 W with 16 dB gain @ 945 MHz
- BeO free package
- In compliance with the 2002/95/EC European directive
- Bidirectional ESD



The LET9070FB is a common source N-channel enhancement mode lateral field-effect RF power transistor designed for broadband commercial and industrial applications at frequencies up to 1.0 GHz. The LET9070FB is designed for high gain and broadband performance operating in common source mode at 28 V. It is ideal for base station applications requiring high linearity.

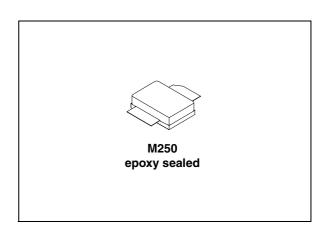


Figure 1. Pin out

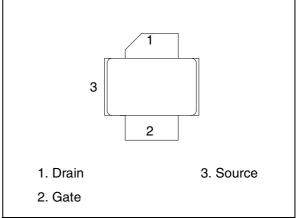


Table 1. Device summary

Order code	Package	Branding
LET9070FB	M250	LET9070FB

Maximum ratings LET9070FB

### 1 Maximum ratings

Table 2. Absolute maximum ratings ( $T_{CASE} = 25 \, ^{\circ}C$ )

Symbol	Parameter	Value	Unit
V <sub>(BR)DSS</sub>	Drain-source voltage	80	V
$V_{GS}$	Gate-source voltage	-10 to +15	V
I <sub>D</sub>	Drain current	12	Α
P <sub>DISS</sub>	Power dissipation (@ T <sub>C</sub> = 70 °C)	130	W
TJ	Max. operating junction temperature	200	°C
T <sub>STG</sub>	Storage temperature	-65 to +150	°C

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R <sub>th(JC)</sub>	Junction-case thermal resistance	1.0	°C/W

#### 2 Electrical characteristics

T<sub>C</sub> = 25 °C

Table 4. Static

Symbol	Test conditions	Min.	Тур.	Max.	Unit
V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0; I <sub>DS</sub> = 10 mA	80			V
I <sub>DSS</sub>	V <sub>GS</sub> = 0; V <sub>DS</sub> = 28 V			1	μА
I <sub>GSS</sub>	$V_{GS} = 5; V_{DS} = 0$			1	μА
V <sub>GS(Q)</sub>	$V_{DS} = 28; I_D = 100 \text{ mA}$	2.0		5.0	V
V <sub>DS(ON)</sub>	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 3 A		0.8	1.2	V
G <sub>FS</sub>	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 3 A	2.5			mho
C <sub>ISS</sub>	V <sub>GS</sub> = 0; V <sub>DS</sub> = 28 V; f = 1 MHz		78		pF
C <sub>OSS</sub>	V <sub>GS</sub> = 0; V <sub>DS</sub> = 28 V; f = 1 MHz		42		pF
C <sub>RSS</sub>	V <sub>GS</sub> = 0; V <sub>DS</sub> = 28 V; f = 1 MHz		2.7		pF

Table 5. Dynamic

Symbol	Test conditions	Min.	Тур.	Max.	Unit
P <sub>OUT</sub>	$V_{DD} = 28 \text{ V}; I_{DQ} = 400 \text{ mA}; P_{IN} = 2.5 \text{ W}; f = 945 \text{ MHz}$	70	80		W
G <sub>PS</sub>	$V_{DD} = 28 \text{ V}; I_{DQ} = 400 \text{ mA}; P_{OUT} = 70 \text{ W}; f = 945 \text{ MHz}$		16		dB
h <sub>D</sub>	$V_{DD} = 28 \text{ V}; I_{DQ} = 400 \text{ mA}; P_{IN} = 2.5 \text{ W}; f = 945 \text{ MHz}$	60	65		%
Load mismatch	$V_{DD}$ = 35 V; $I_{DQ}$ = 400 mA; $P_{OUT}$ = 100 W; f = 945 MHz All phase angles		20:1		VSWR

Impedance data LET9070FB

### 3 Impedance data

Figure 2. Impedance data

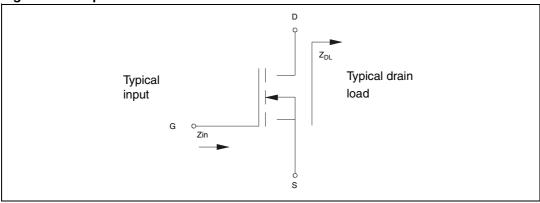


Table 6. Impedance data

Frequency	<b>Z</b> <sub>IN</sub> (Ω)	Z <sub>OUT</sub> (Ω)
945	TBD	TBD

#### 4 Typical performance

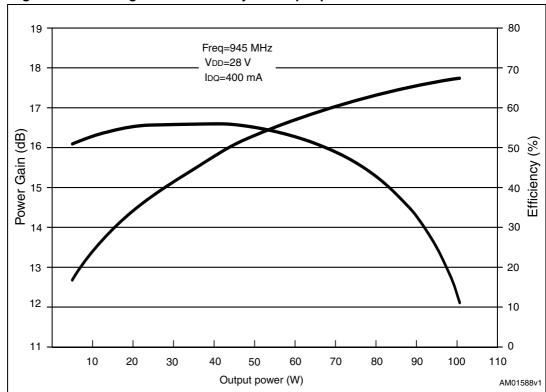


Figure 3. Power gain and efficiency vs. output power

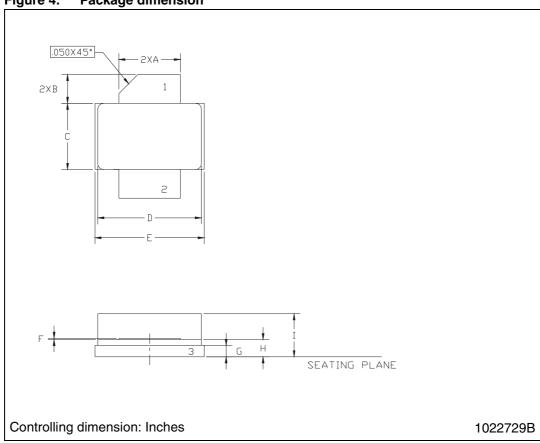
### 5 Package mechanical data

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Table 7. M250 (.230 x .360 2L N/HERM W/FLG) mechanical data

Dim.	mm.		Inch			
	Min	Тур	Max	Min	Тур	Max
Α	5.21		5.71	0.205		0.225
В	2.16		2.92	0.085		0.115
С	5.59		6.09	0.220		0.240
D	8.89		9.40	0.350		0.370
Е	9.40		9.91	0.370		0.390
F	0.11		0.15	0.004		0.006
G	0.89		1.14	0.035		0.045
Н	1.45		1.70	0.057		0.067
I	2.67		3.94	0.105		0.155

Figure 4. Package dimension



**577** 

Revision history LET9070FB

## 6 Revision history

Table 8. Document revision history

Date	Revision	Changes
20-Dec-2012	1	Initial release.

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